

Customer No.: 31561
Application No.: 10/708,371
Docket NO.: 11955-US-PA

AMENDMENT

In the Specification:

Claim 1 (currently amended) A power amplifier with an active bias circuit, comprising:

a power amplifier transistor with a gate connected to a gate bias voltage; and

an active bias circuit connected to an input power terminal and the gate of the power amplifier transistor for receiving an input power from the input power terminal and outputting the gate bias voltage to the gate, wherein the gate bias voltage is increased corresponding to an increase of the input power, wherein the active bias circuit comprises a voltage source.

Claim 2 (original) The power amplifier of claim 1, wherein a curve of an increase of the gate bias voltage versus the input power is a linear curve.

Claim 3 (original) The power amplifier of claim 1, wherein a curve of an increase of the gate bias voltage versus the input power is a non-linear curve.

Claim 4 (original) The power amplifier of claim 1, wherein the power amplifier

Customer No.: 31561
Application No.: 10/708,371
Docket NO.: 11955-US-PA

transistor and the active bias circuit is manufactured by a system on chip (SOC) process.

Claim 5 (original) The power amplifier of claim 1, wherein the active bias circuit comprises a diode and a resistor.

Claim 6 (original) The power amplifier of claim 5, wherein an equivalent resistance of the diode in the active bias circuit varies in correspondence with the input power.

Claim 7 (currently amended) An integrated circuit for a power amplifier with an active bias circuit, comprising:

a power output device;
a power amplifier transistor with a gate connected to a gate bias voltage;
an active bias circuit connected to the power output device and the gate of the power amplifier transistor for receiving an input power from the power output device and providing a gate bias voltage to the gate, wherein the gate bias voltage is increased corresponding to an increase of the input power, wherein the active bias circuit comprises a voltage source; and

Customer No.: 31561
Application No.: 10/708,371
Docket NO.: 11955-US-PA

a power input device connected to an output terminal of the power amplifier transistor for receiving an amplified output power from the power amplifier transistor.

Claim 8 (original) The integrated circuit of claim 7, wherein a curve of an increase of the gate bias voltage versus the input power is a linear curve.

Claim 9 (original) The integrated circuit of claim 7, wherein a curve of an increase of the gate bias voltage versus the input power is a non-linear curve.

Claim 10 (original) The integrated circuit of claim 7, wherein the power amplifier transistor and the active bias circuit is manufactured by a system on chip (SOC) process.

Claim 11 (original) The integrated circuit of claim 7, wherein the active bias circuit comprises a diode and a resistor.

Claim 12 (original) The integrated circuit of claim 11, wherein the equivalent resistance of the diode in the active bias circuit varies in correspondence with the input power.

Customer No.: 31561
Application No.: 10/708,371
Docket NO.: 11955-US-PA

Claim 13 (currently amended) A method for generating a gate bias voltage of a power amplifier transistor corresponding to an input power, comprising:

providing an input power; and

outputting a gate bias voltage corresponding to the input power, wherein the gate bias voltage is powered by a voltage source other than the input power and increased corresponding to an increase of the input power.

Claim 14 (original) The method of claim 13, wherein a curve of an increase of the gate bias voltage versus the input power is a linear curve.

Claim 15 (original) The method of claim 13, wherein a curve of an increase of the gate bias voltage versus the input power is a non-linear curve.

Claim 16 (new) The power amplifier of claim 1, wherein the active bias circuit comprises a grounded level.

Claim 17 (new) The method of claim 7, wherein the active bias circuit comprises a grounded level.